



NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

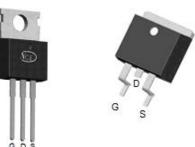
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

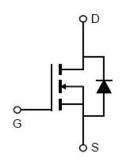
General Features

- V_{DS} =200V, I_D =125A $R_{DS(ON)}$ =7.7m Ω , typical (TO-220)@ V_{GS} =10V $R_{DS(ON)}$ =7.5m Ω , typical (TO-263)@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!







Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP090N20	NCEP090N20	TO-220-3L	-	-	-
NCEP090N20D	NCEP090N20D	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	200	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	125	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	88	А
Pulsed Drain Current	I _{DM}	500	А
Maximum Power Dissipation	P _D	340	W
Derating factor		2.27	W/°C
Single pulse avalanche energy (Note 1)	E _{AS}	1692	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

ermal Resistance,Junction-to-Case	Rejc	0.44	°C/W
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics	'			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA		200	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V,V	V _{DS} =200V,V _{GS} =0V		-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$		2.0	3.0	4.0	V
Desire Course On Otata Basistan		1011	TO-220	-	7.7	9.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	TO-263	-	7.5	9.0	
Forward Transconductance	g FS	V _{DS} =10V,I _D	=20A	70	-	-	S
Dynamic Characteristics	-			1			
Input Capacitance	C _{lss}	- V _{DS} =100V,V _{GS} =0V, - F=1.0MHz		-	6000	-	PF
Output Capacitance	Coss			-	535	-	PF
Reverse Transfer Capacitance	C _{rss}			-	17.5	-	PF
Switching Characteristics (Note 2)	·						
Turn-on Delay Time	t _{d(on)}	V_{DD} =100V, I_{D} =20A V_{GS} =10V, R_{G} =4.7 Ω		-	54	-	nS
Turn-on Rise Time	t _r			-	38	-	nS
Turn-Off Delay Time	t _{d(off)}			-	65	-	nS
Turn-Off Fall Time	t _f			-	15	-	nS
Total Gate Charge	Qg	V _{DS} =100V,I _D =20A, V _{GS} =10V		-	95		nC
Gate-Source Charge	Qgs			-	30.5		nC
Gate-Drain Charge	Q _{gd}			-	24.5		nC
Drain-Source Diode Characteristics	1			•	'		•
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =20A		-		1.2	V
Diode Forward Current	Is			-	-	125	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 50A		-	98		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs		-	260		nC

Notes:

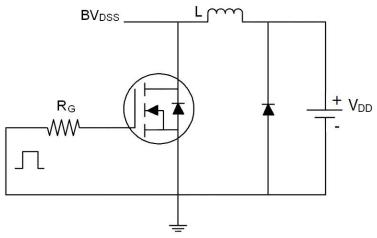
- 1. EAS condition : Tj=25 $^{\circ}\text{C}\text{,V}_{DD}\text{=}50\text{V}\text{,V}_{G}\text{=}10\text{V}\text{,L=}0.5\text{mH}\text{,Rg=}25\Omega$
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heat sink, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.



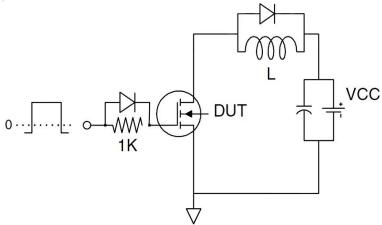


Test Circuit

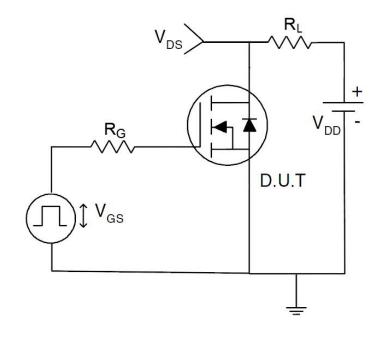
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

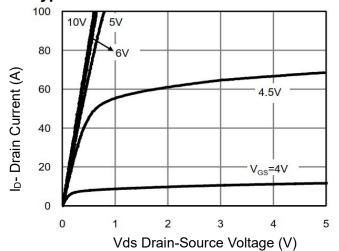


Figure 1 Output Characteristics

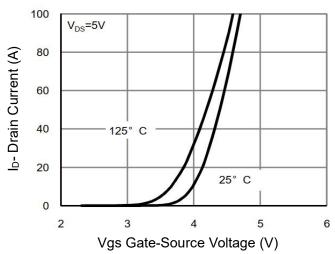


Figure 2 Transfer Characteristics

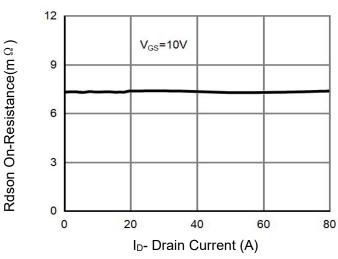


Figure 3 Rdson- Drain Current

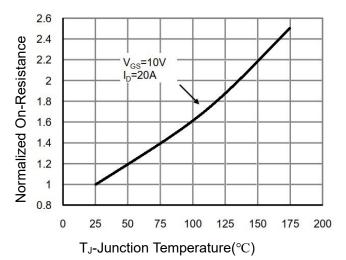


Figure 4 Rdson-JunctionTemperature

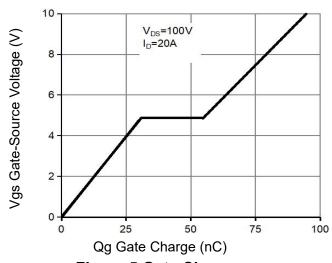


Figure 5 Gate Charge

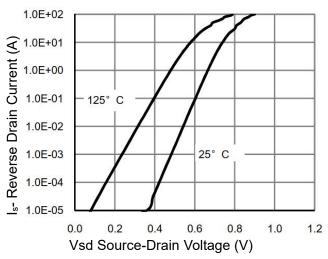
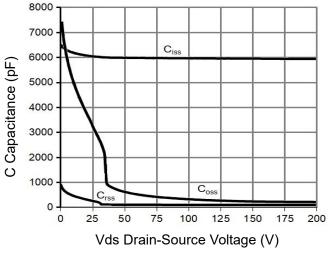


Figure 6 Source- Drain Diode Forward







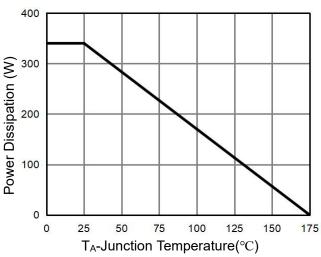
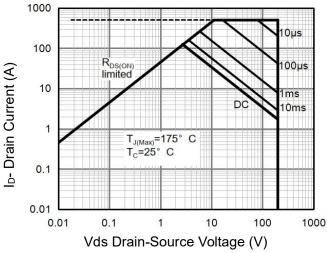


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



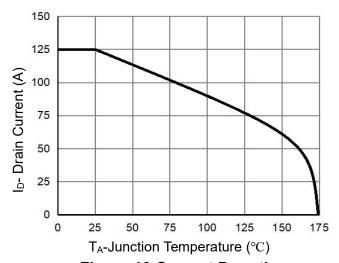
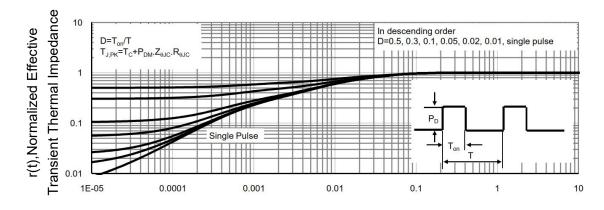


Figure 8 Safe Operation Area (Note3)

Figure 10 Current De-ratin

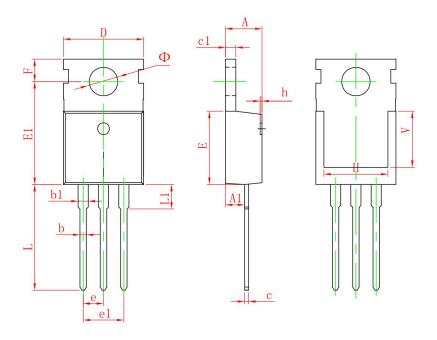


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



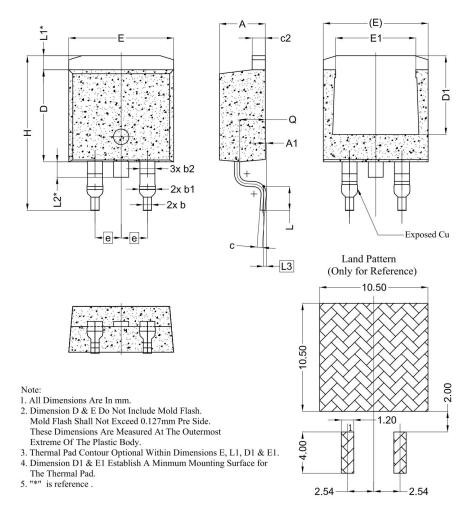
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.950	9.750	0.352	0.384	
E1	12.650	13.050	0.498	0.514	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900	REF.	0.276 REF.		
Φ	3.400	3.800	0.134	0.150	



TO-263-2L Package Information



SYMBOL	DIMENSIONS				
	MIN.	NOM.	MAX.		
А	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1.20	1.20 1.45			
С	0.40	0.50	0.60		
c2	1.15	1.27	1.40		
D	8.82	8.92	9.02		
D1	6.86 7.65		-		
Е	9.96 10.16		10.36		
E1	6.89	7.77	7.89		
е	2.54 BSC				
Н	14.61	15.00	15.88		
L	1.78	2.32	2.79		
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30 2.48 2.70				



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